

P-Channel Enhancement Mode Power MOSFET

Description

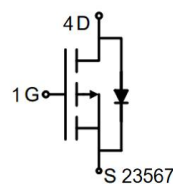
The GT065P06M6 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

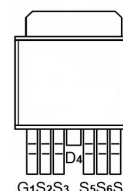
- V_{DS} -60V
- I_D (at $V_{GS} = -10V$) -103A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 7.5m Ω
- $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) < 9.5m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

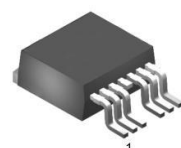
- Power switch
- DC/DC converters



Schematic diagram



pin assignment



TO-263-6

Ordering Information

Device	Package	Marking	Packaging
GT065P06M6	TO-263-6	GT065P06	800psc/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$ -103	A
		$T_C = 100^\circ\text{C}$ -65	
Pulsed Drain Current (note1)	I_{DM}	-412	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	178	W
Single pulse avalanche energy (note2)	E_{AS}	272	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	R_{thJC}	0.7	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-60	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.7	-2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -20A	--	6.0	7.5	mΩ
		V _{GS} = -4.5V, I _D = -15A	--	7.7	9.5	
Forward Transconductance	g _{FS}	V _{DS} = -5V, I _D = -20A	--	51	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -30V, f = 1.0MHz	--	5985	--	pF
Output Capacitance	C _{oss}		--	907	--	
Reverse Transfer Capacitance	C _{rss}		--	42	--	
Total Gate Charge	Q _g	V _{DD} = -30V, I _D = -20A, V _{GS} = -10V	--	99	--	nC
Gate-Source Charge	Q _{gs}		--	13	--	
Gate-Drain Charge	Q _{gd}		--	21	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = -30V, I _D = -20A, R _G = 3Ω	--	20	--	ns
Turn-on Rise Time	t _r		--	18	--	
Turn-off Delay Time	t _{d(off)}		--	55	--	
Turn-off Fall Time	t _f		--	35	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	-103	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = -20A, V _{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = -20A, V _{GS} = 0V di/dt=-100A/us	--	71	--	nC
Reverse Recovery Time	T _{rr}		--	49	--	ns

Notes

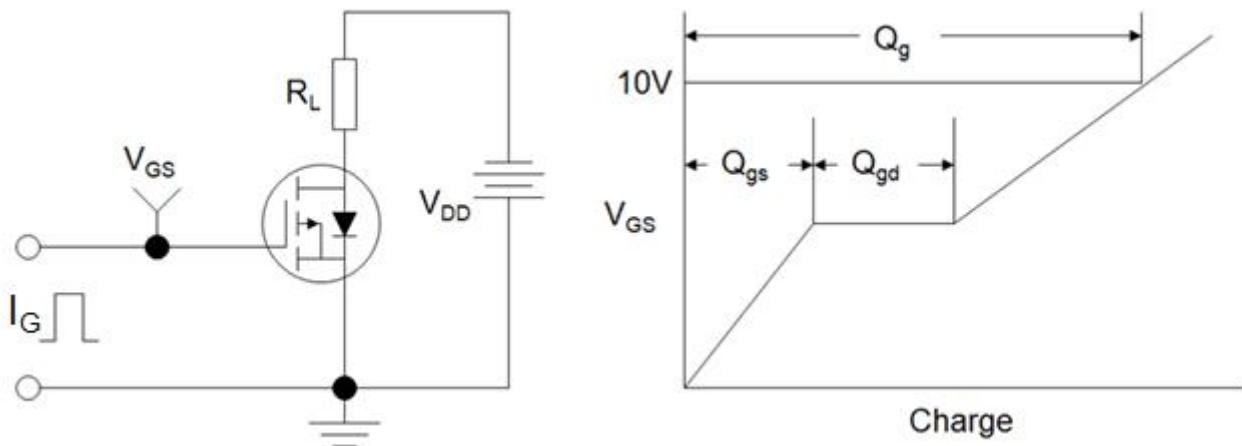
1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition : $T_J = 25^{\circ}\text{C}$, $V_{DD} = -50V$, $V_{GS} = -10V$, $L = 0.5\text{mH}$, $R_g = 25\Omega$

The table shows the minimum avalanche energy, which is 702mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

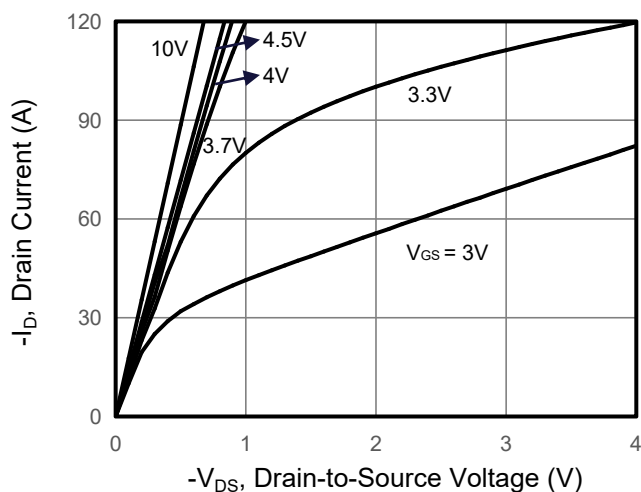


Figure 2. Transfer Characteristics

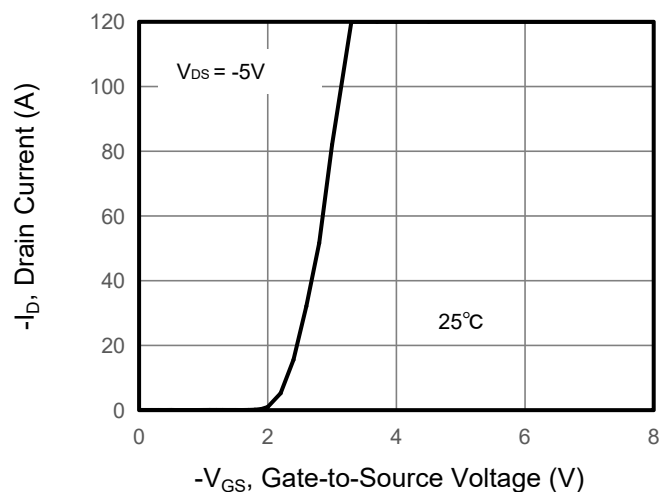


Figure 3. Drain Source On Resistance

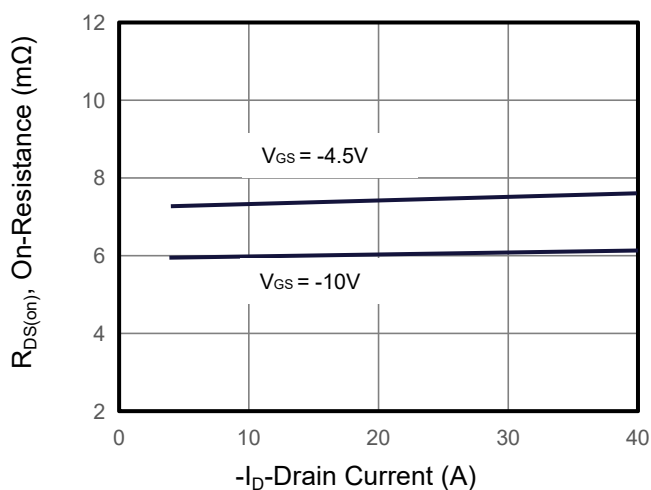


Figure 4. Gate Charge

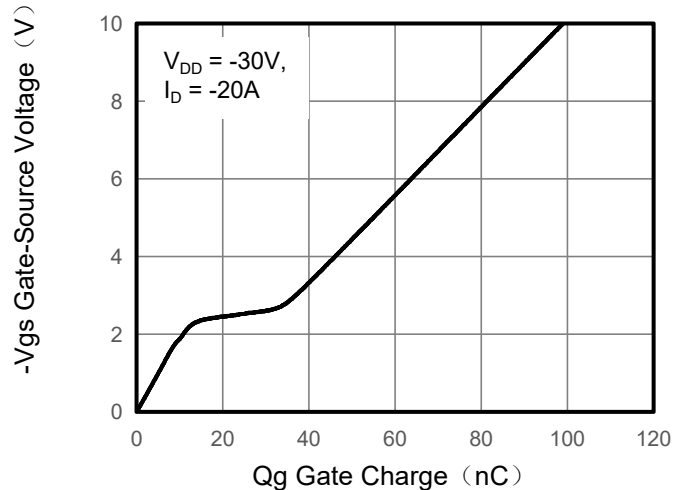


Figure 5. Capacitance

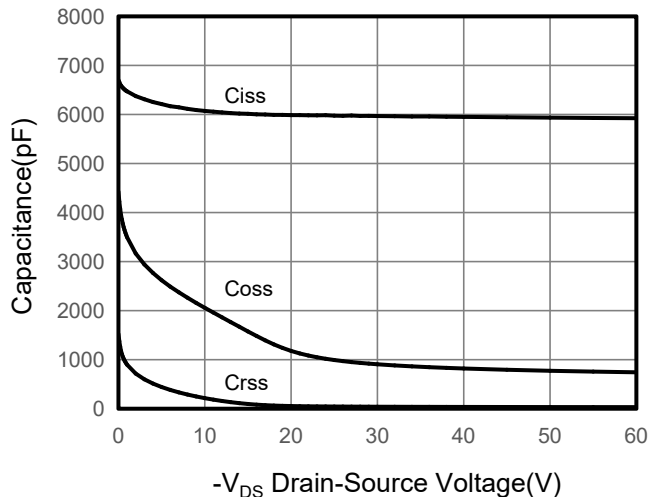
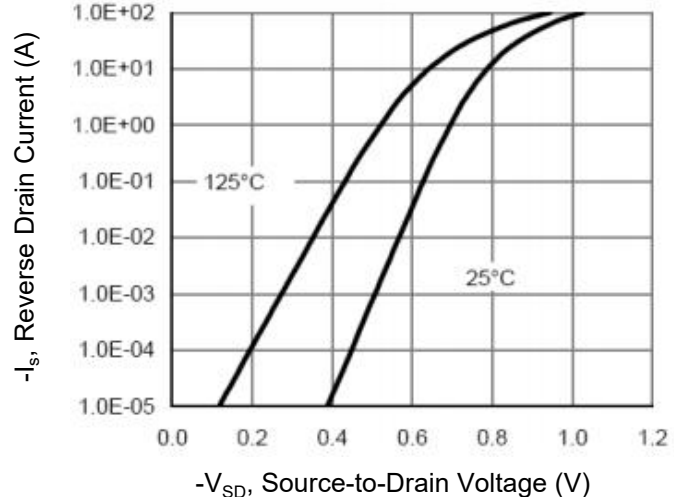


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

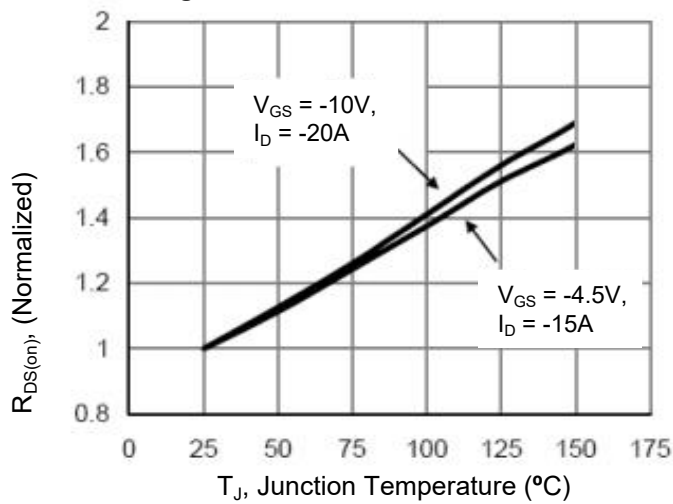


Figure 8. Safe Operation Area

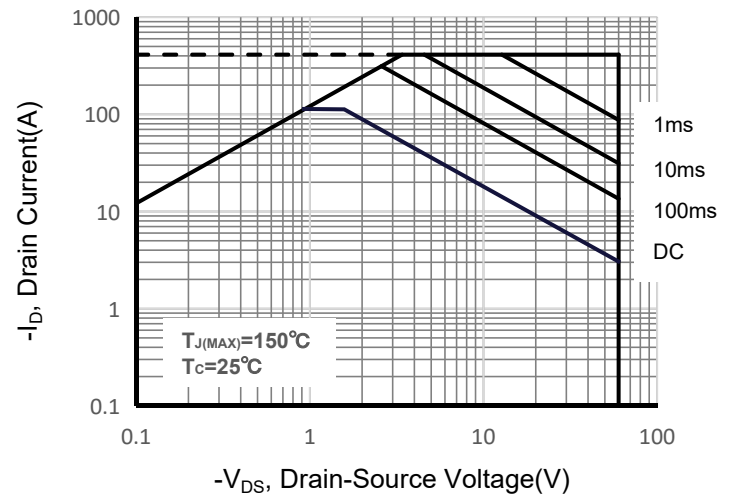


Figure 9. Maximum Continuous Drain Current vs Case Temperature

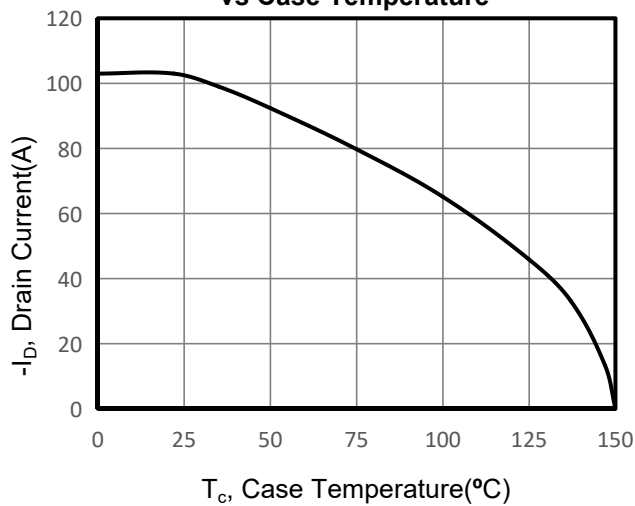
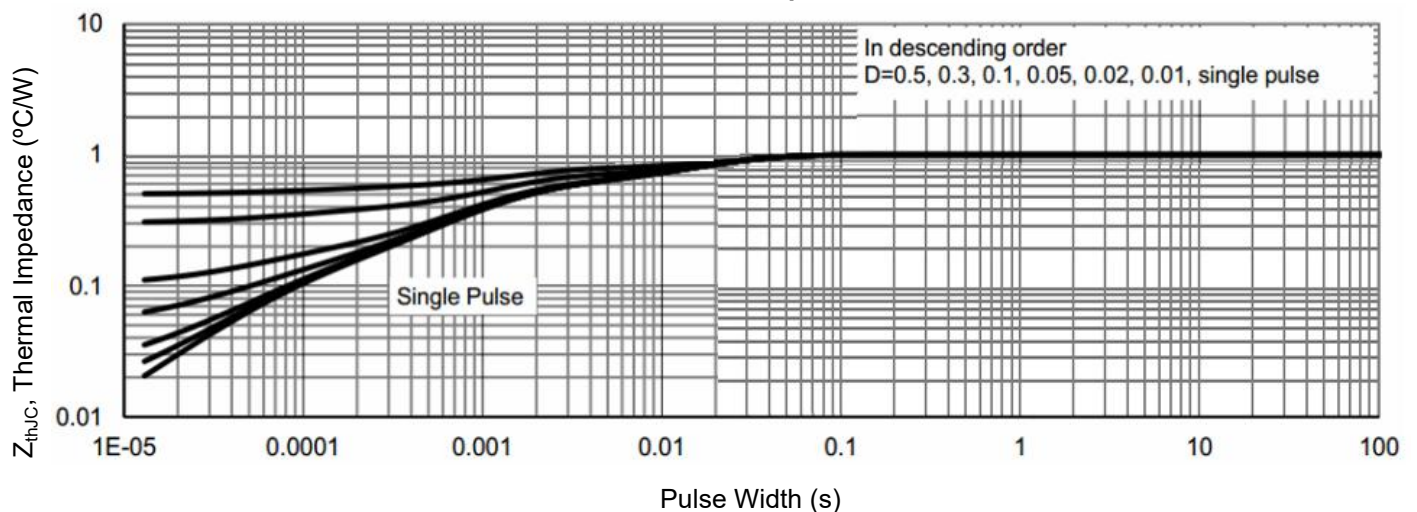
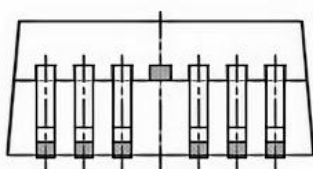
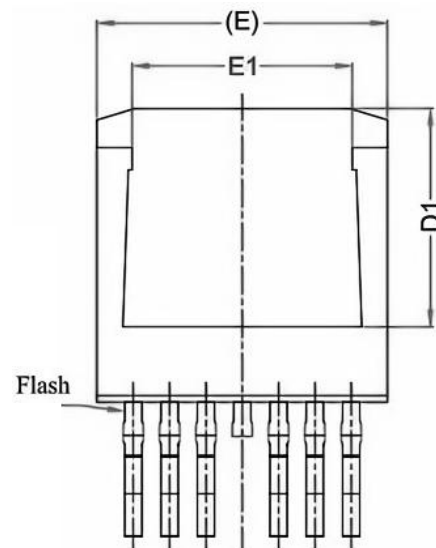
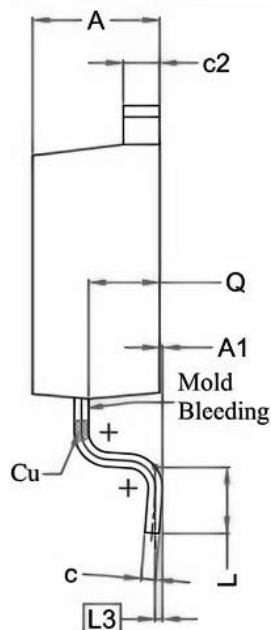
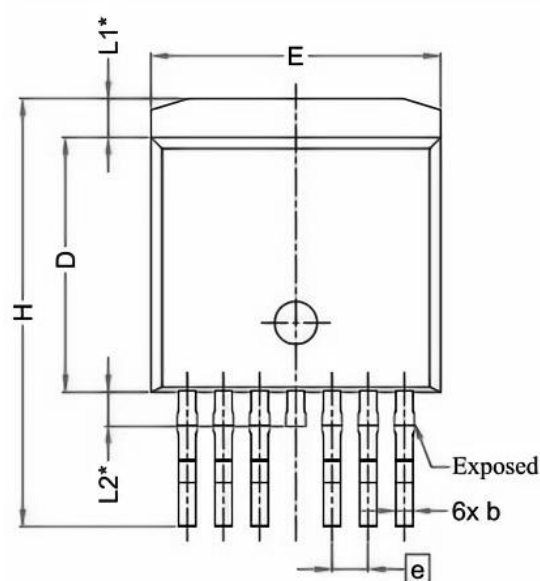


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-263-6 Package Information



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	---
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70